

## PENDING CLAIMS

The following is a list of currently pending claims. Claims 2, 9, 15, and 17-19 are amended as shown. Claim 14 is cancelled.

1. (Cancelled)
2. (Currently amended) The method of claim 17 wherein the temperature is ~~between about 450 and less than or~~ about 480 degrees Celsius.
3. (Original) The method of claim 2 wherein pressure is between about 200 mTorr and about 1 Torr.
4. (Original) The method of claim 3 wherein an inert gas is flowed over the surface with the SiH<sub>4</sub> and BCl<sub>3</sub>.
5. (Original) The method of claim 4 wherein the inert gas is helium.
6. (Cancelled)
7. (Previously amended) The method of claim 18, wherein the second source gas comprises about 0.1 percent BCl<sub>3</sub> or more.
8. (Original) The method of claim 7, wherein the second source gas further comprises an inert gas.
9. (Currently amended) The method of claim 8, wherein the temperature is ~~between about 450 less than or~~ about 480 degrees Celsius.
10. (Original) The method of claim 9, wherein the inert gas is helium.

11. (Original) The method of claim 8, wherein the pressure is between about 200 mTorr and about 1 Torr.
12. (Cancelled)
13. (Currently amended) The method of claim 19 wherein the step of depositing the polysilicon film comprises substantially simultaneously flowing SiH<sub>4</sub> and BCl<sub>3</sub> over the surface.
14. (Cancelled)
15. (Currently amended) The method of claim 14 13 wherein the temperature is between about 450 and less than or about 480 degrees Celsius.
16. (Original) The method of claim 15 wherein the pressure is between 200 mTorr and 1 Torr.
17. (Currently amended) A method for depositing a doped polysilicon film comprising:  
providing a surface; and  
substantially simultaneously flowing SiH<sub>4</sub> and BCl<sub>3</sub> over the surface at a temperature less than or equal to between about 460 and about 500 degrees Celsius under conditions that achieve an average concentration in the doped polysilicon film of between about  $7 \times 10^{20}$  and about  $3 \times 10^{21}$  boron atoms per cubic centimeter, wherein the doped polysilicon film is polycrystalline as deposited.
18. (Currently Amended) A method for forming an in-situ doped polysilicon film, the method comprising:  
providing a surface; and

substantially simultaneously flowing a first source gas comprising SiH<sub>4</sub> and a second source gas comprising BCl<sub>3</sub> over the surface at a temperature ~~less than~~ between about 460 and about 500 degrees Celsius under conditions sufficient to achieve in the doped polysilicon an average concentration of between about 7 x 10<sup>20</sup> and about 3 x 10<sup>21</sup> boron atoms per cubic centimeter, wherein during this flowing step, polycrystalline silicon is deposited.

19. (Currently amended) A method for depositing an in-situ doped polysilicon film comprising:

providing a substrate comprising a substantially horizontal surface and a substantially vertical sidewall descending from the horizontal surface, the sidewall having a top; and

depositing the in-situ doped polysilicon film on the surface at a temperature ~~less than~~ between about 460 and about 500 degrees Celsius, wherein:

a first thickness of the film at its thinnest point on the vertical sidewall is at least 80 percent of a second thickness of the film on the sidewall at the top of the sidewall, and

a third thickness of the film on the horizontal surface is at least 200 angstroms,

wherein an average concentration of boron atoms in the polysilicon is between about 7 x 10<sup>20</sup> and about 3 x 10<sup>21</sup> per cubic centimeter,

and wherein, during the depositing step, doped polycrystalline silicon is deposited.